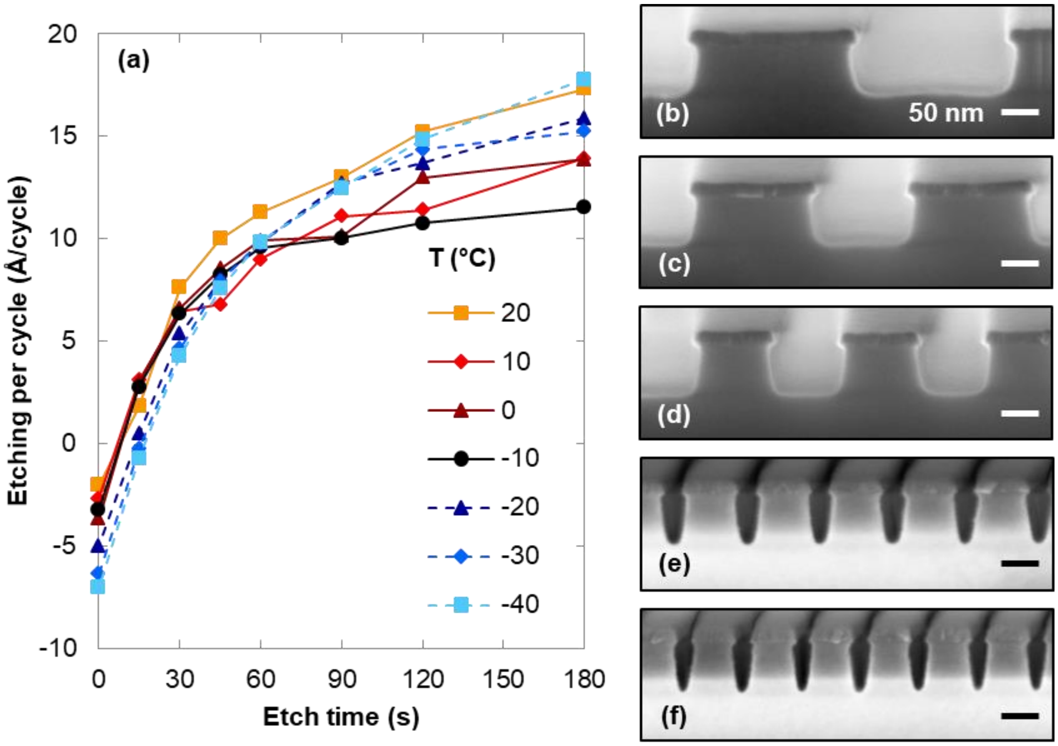

Figure 1. (a) SiO_2 ALE under increased Ar plasma etch time at different temperatures and at low electrode voltage (-9 V). At -10°C ALE is self-limiting. (b)-(f) SiO_2 etching of features between 20 nm and 200 nm with 60 cycles CHF_3-based ALE using 15 nm lift-off chromium mask.